

# Schottky barrier diode

## RB531XN

### ●Applications

Rectifying small power

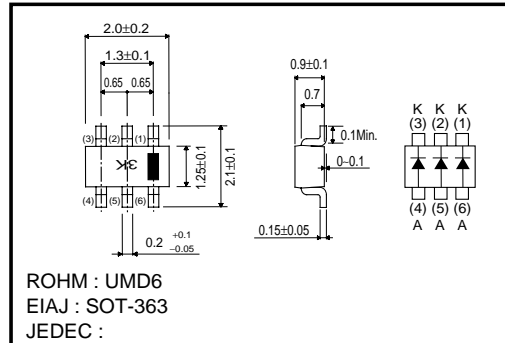
### ●Features

- 1) Small mold type. (UMD6)
- 2) High reliability.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Unit : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	30	V
Mean rectifying current *1	$I_O$	100	mA
Peak forward surge current *2	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

\*1 Rating of per diode.

\*2 60Hz for 1  $\varnothing$

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	–	–	0.300	V	$I_F=10\text{mA}$
	$V_{F2}$	–	–	0.430	V	$I_F=100\text{mA}$
Reverse current	$I_R$	–	–	20	$\mu\text{A}$	$V_R=10\text{V}$

Note) Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

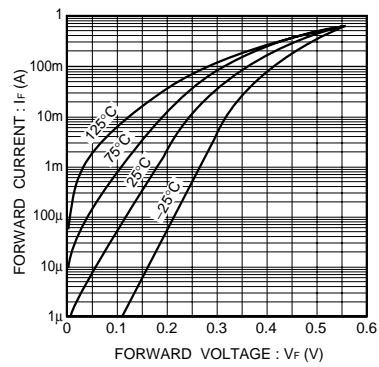


Fig.1 Forward characteristics

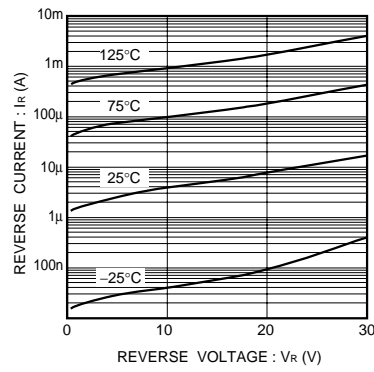


Fig.2 Reverse characteristics

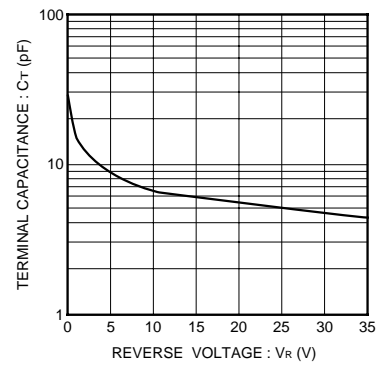


Fig.3 Capacitance between terminals characteristics